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1/5/04
(Date of Deposit)

Karen Cinq-Mars
Karen Cinq-Mars (Signature)

1/5/04
(Date)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re Application of : January 5, 2004
Furukawa et al. :
Serial No. 10/707,009 : Examiner:
Filed: Herewith : IBM Corporation
Dept. 18G/Bldg. 300-482
Title: ALTERNATING PHASE MASK BUILT : 2070 Route 52
BY ADDITIVE FILM DEPOSITION : Hopewell Junction,
New York 12533-6531

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P. O. Box 1450
Alexandria, VA 22313-1450

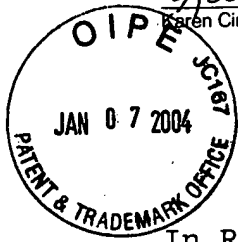
Sir:

In compliance with the duty of disclosure under
37 C.F.R. § 1.56 and in accordance with the practice under
37 C.F.R. §§ 1.97 and 1.98, the Examiner's attention is directed to
the documents listed on the enclosed Form PTO-1449. Copies of the
listed documents are also enclosed.

It is respectfully requested that the above information be
considered by the Examiner and that a copy of the enclosed Form
PTO-1449 be returned indicating that such information has been
considered.

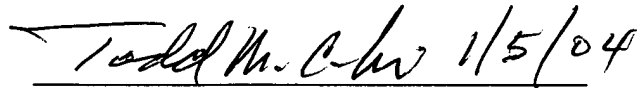
Applicants undersigned attorney may be reached by telephone

FIS920030300



at (845) 894-6919. All correspondence should continue to be directed to the below listed address.

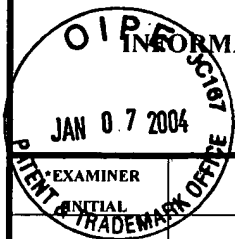
Respectfully submitted,

 Todd M. C. Li 1/5/04

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INTERNATIONAL BUSINESS MACHINES CORPORATION
Intellectual Property Law Department
B/300-482
2070 Route 52
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TML/kcm

**INFORMATION DISCLOSURE CITATION***(Use several sheets if necessary)*

Docket Number (Optional)

FIS920030300

Application Number

10/707,009

Applicant(s)

Furukawa et al.

Filing Date

11-13-03

Group Art Unit

OTHER DOCUMENTS *(Including Author, Title, Date, Pertinent Pages, Etc.)*

Homma et al., "A Selective SiO₂ Film-Formation Technology Using Liquid-Phase Deposition for Fully Planarized Multilevel Interconnections", J. Electrochem. Cos., Vol. 140, No. 8, 1993, pp. 2410-2414.

Ching-Fa Yeh, et al., "Comprehensive Investigation on Fluorosilicate Glass Prepared by Temperature-Difference-Based Liquid-Phase Deposition", J. Electrochem. Soc., Vol. 147, No. 1, 2000, pp. 330-334.

Nagayama et al., "A New Process for Silica Coating", J. Electrochem. Soc., Vol. 135, No. 8, 1988, pp. 2013-2016.

Homma et al., "Optical Properties of Fluorinated Silicon Oxide and Organic Spin-on-Glass Films for Thin-Film Optical Waveguides", J. Electrochem. Soc., Vol. 147, No. 3, 2000, pp. 1141-1144.

Ching-Fa Yeh et al., "Novel Barrier Dielectric Liner Prepared by Liquid-Phase Deposition and NH₃ Plasma Annealing", Journal of Appl. Phys. Vol. 39, 2000, pp. 6672-6675.

EXAMINER**DATE CONSIDERED**

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.